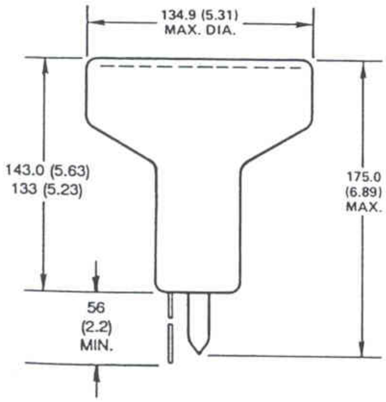
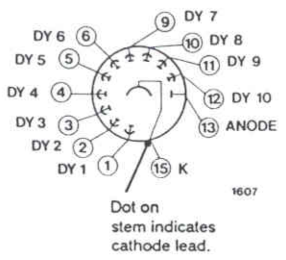
Applied Anode To Cathode Voltage (V)	Voltage Divider[1]	Luminous Responsivity Min. (A/lm)	Luminous Responsivity Typ. (A/lm)	Filtered Responsivity Min. (A/ inc lm)	Filtered Responsivity Typ. (A/ inc lm)	Typ. Curr. Amp. (Gain) (x10⁶)	Typ. Rise Time (ns)	Typ. Transit Time (ns)	Anode Dark Current @ 22° C Test Cond. (A/lm)	Anode Dark Current Typ. (nA)	Anode Dark Current Max. (nA)	Pulse Characteristics: Applied Anode To Cathode Voltage (V)	Isotope	Pulse Height Res. Typ. (%)	Pulse Height Typ. (mV)
1100	D1	--	--	0.35[2]	0.95[2]	.095			10	1.0	10	1100	^{57}Co	8.8	125
1100	D1	--	--	0.35[2]	0.95[2]	.095			10	1.0	10	1100	^{57}Co	8.8	125
1100	D	--	--	0.3[2]	0.8[2]	0.067	22	105	9	1.0	50	1100	^{137}Cs	6.9	155
1100	D	--	--	0.3[2]	0.8[2]	0.067	22	105	9	1.0	50	1100	^{137}Cs	6.9	155
2000	Q	--	2850	100[2]	400[2]	51	4	78	2000	60	600	Not Applicable			

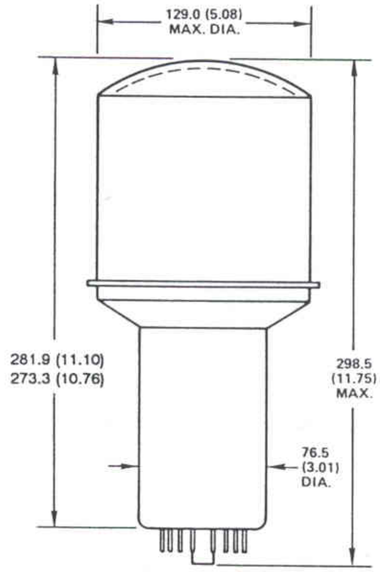
S83006EM2

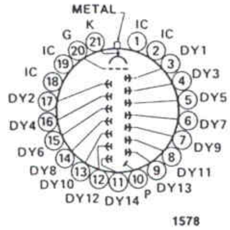




Note: If temporary base is required order S83006EM1. Basing is identical to that for S83006E.

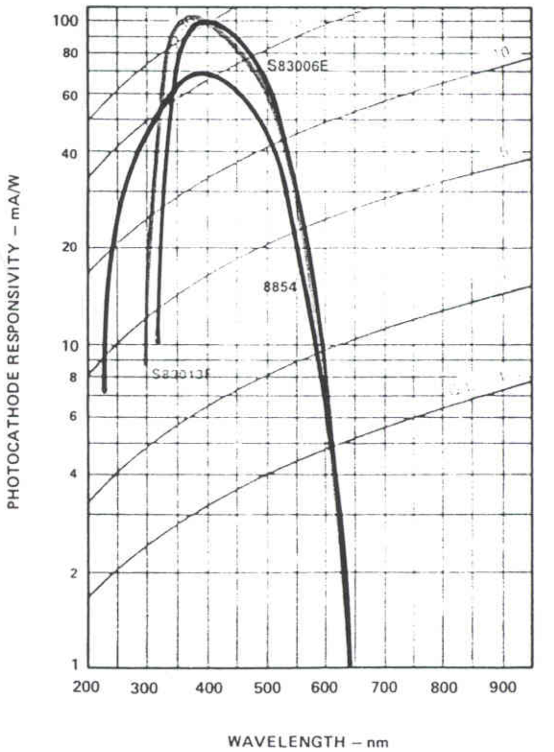
8854



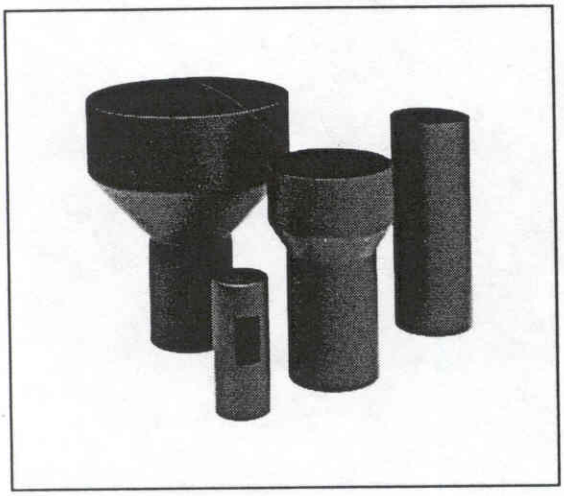


Socket - BURLE AJ2145A (Supplied)
BURLE AJ2144A (Optional)
Magnetic Shield - BURLE AJ2255

Typical Photocathode Spectral Response Characteristics



TP-107
Magnetic Shields



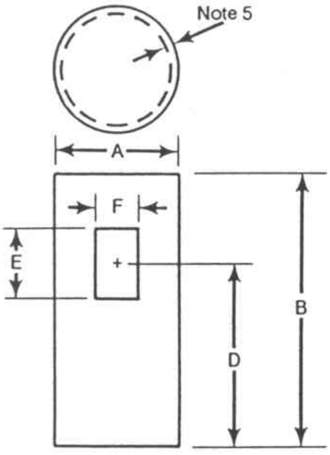
Magnetic Shields for Photomultipliers

- Minimizes Effects of Spurious Magnetic Fields
- High Permeability
- Available for Most BURLE PMTs

Spurious magnetic fields can negatively influence the performance characteristics of any photomultiplier. This is due to the effect the magnetic flux has in de-focussing the electron-stream in the spacings between electrodes. This is particularly true in the cathode-to-dynode 1 region of most photomultipliers. Flux densities, even as low as the earth's magnetic field which is on the order of 1 gauss or less, can create unreliable results when detecting the low-light levels for which photomultipliers are so well suited.

The BURLE AJ-series of magnetic shields are specifically designed to minimize the effects of most spurious magnetic fields found either naturally or caused by the proximity of other electronic circuits. BURLE magnetic shields are high permeability, single layer magnetic shields with a flat finish (inside and out). Only in cases of extremely high magnetic flux densities would one have to consider alternate methods of magnetic attenuation.

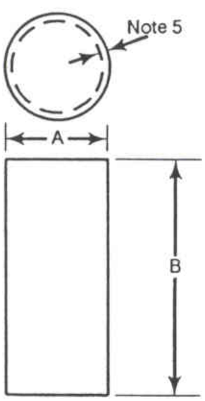
AJ-Series magnetic shields are available for most BURLE photomultipliers.



Dimensions and Descriptions

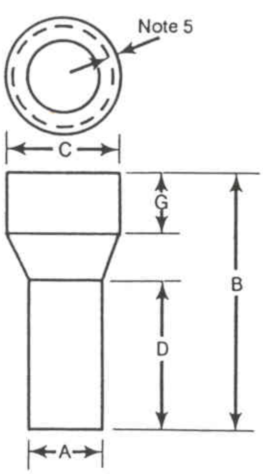
SHIELDS FOR SIDE-WINDOW PHOTOMULTIPLIERS

Magnetic Shield Designation	Inner Diameter	Overall Length	Height from Shield Bottom to Window	Window Dimensions Height	Width	Notes
	A	B	D	E	F	
AJ2240	34.92 (1.375)	82.55 (3.250)	49.20 (1.937)	28.57 (1.125)	15.88 (.625)	1,2,3,4,6
AJ2242	34.92 (1.375)	60.32 (2.375)	31.75 (1.250)	28.57 (1.125)	15.88 (.625)	1,2,3,4,6
AJ2243	44.45 (1.750)	85.72 (3.375)	68.25 (2.687)	22.22 (0.875)	19.05 (.750)	1,2,3,4,6



SHIELDS FOR END-WINDOW PHOTOMULTIPLIERS

Magnetic Shield Designation	Inner Diameter	Overal Length	Notes
	A	B	
AJ2244	25.40 (1.000)	101.60 (4.000)	1,2,3,6
AJ2245	25.40 (1.000)	63.50 (2.500)	1,2,3,6
AJ2246	31.75 (1.250)	114.30 (4.500)	1,2,3,6
AJ2247	44.45 (1.750)	114.30 (4.500)	1,2,3,6
AJ2248	63.50 (2.500)	127.00 (5.000)	1,2,3,6
AJ2249	57.15 (2.250)	127.00 (5.000)	1,2,3,6
AJ2250	57.15 (2.250)	101.60 (4.000)	1,2,3,6
AJ2252	57.15 (2.250)	152.40 (6.000)	1,2,3,6

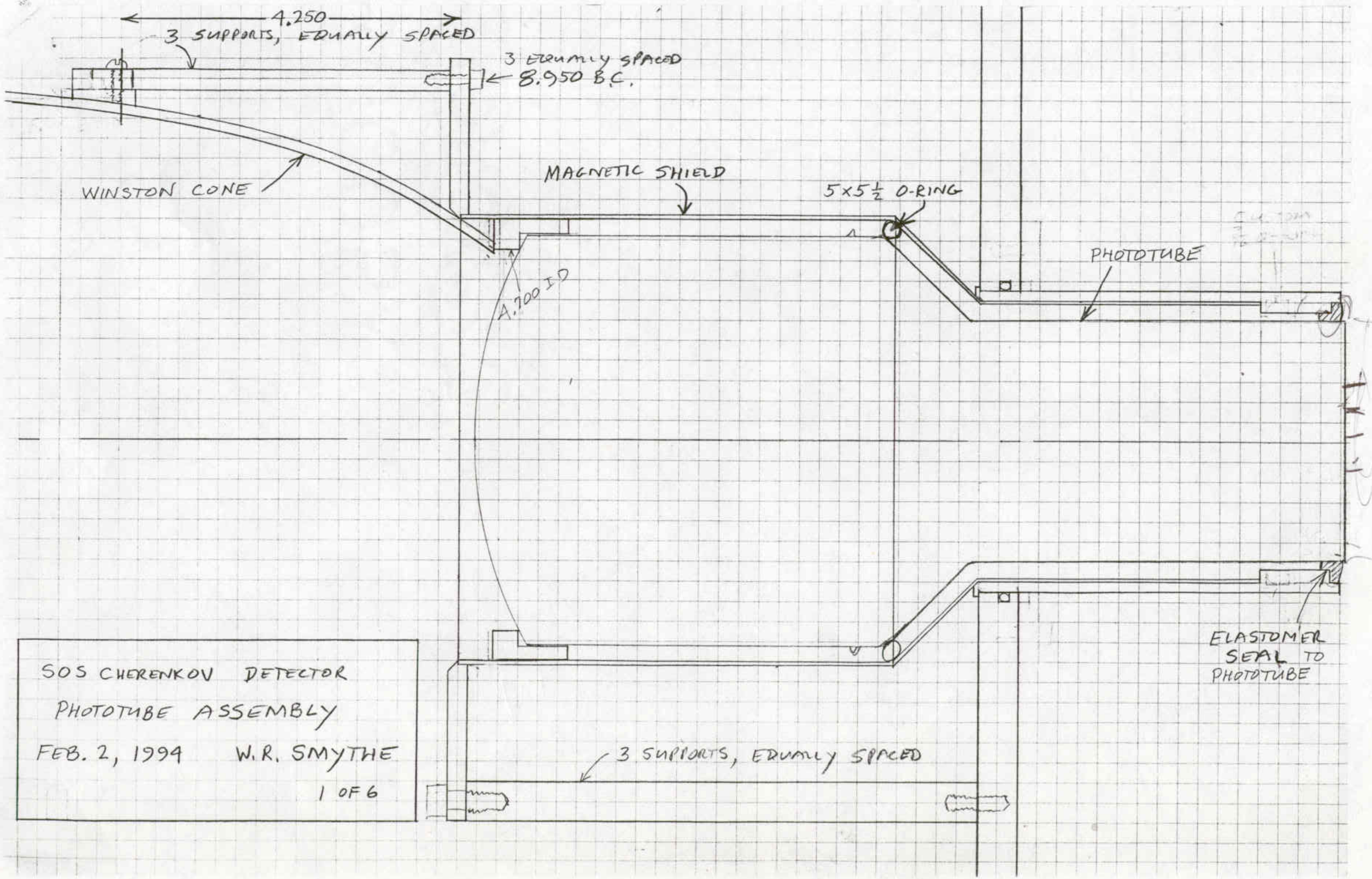


SHIELDS FOR END-WINDOW PHOTOMULTIPLIERS

Magnetic Shield	Neck Inner Diameter	Overall Length	Flare Inner Diameter Designation	Neck Length	Flare Length	Notes
	A	B	C	D	G	
AJ2253	60.32 (2.375)	141.30 (5.562)	83.34 (3.281)	85.72 (3.375)	38.10 (1.500)	1,2,3,6
AJ2254	60.32 (2.375)	174.60 (6.875)	146.00 (5.750)	76.20 (3.000)	50.80 (2.000)	1,2,3,6
AJ2255	82.50 (3.250)	254.00 (10.000)	139.70 (5.500)	88.90 (3.500)	139.70 (5.500)	1,2,3,6

NOTES:

1. Tolerance for shield dimensions shall be as follows:
   Thickness -- $\pm$ 0.051 ($\pm$ 0.002")
   Dimensions -- B,D,E,F & G $\pm$ 0.508 ($\pm$ 0.020")
   Inner diameter -- $\pm$ 0.787 ($\pm$ 0.031")
2. Each shield shall be finished in flat black paint (both inner and outer surfaces).
3. All dimensions are inside dimensions.
4. Upper end closed.
5. All shields have 1.016 (0.040") wall thickness.
6. Dimensions in millimeters (Inches in parentheses).

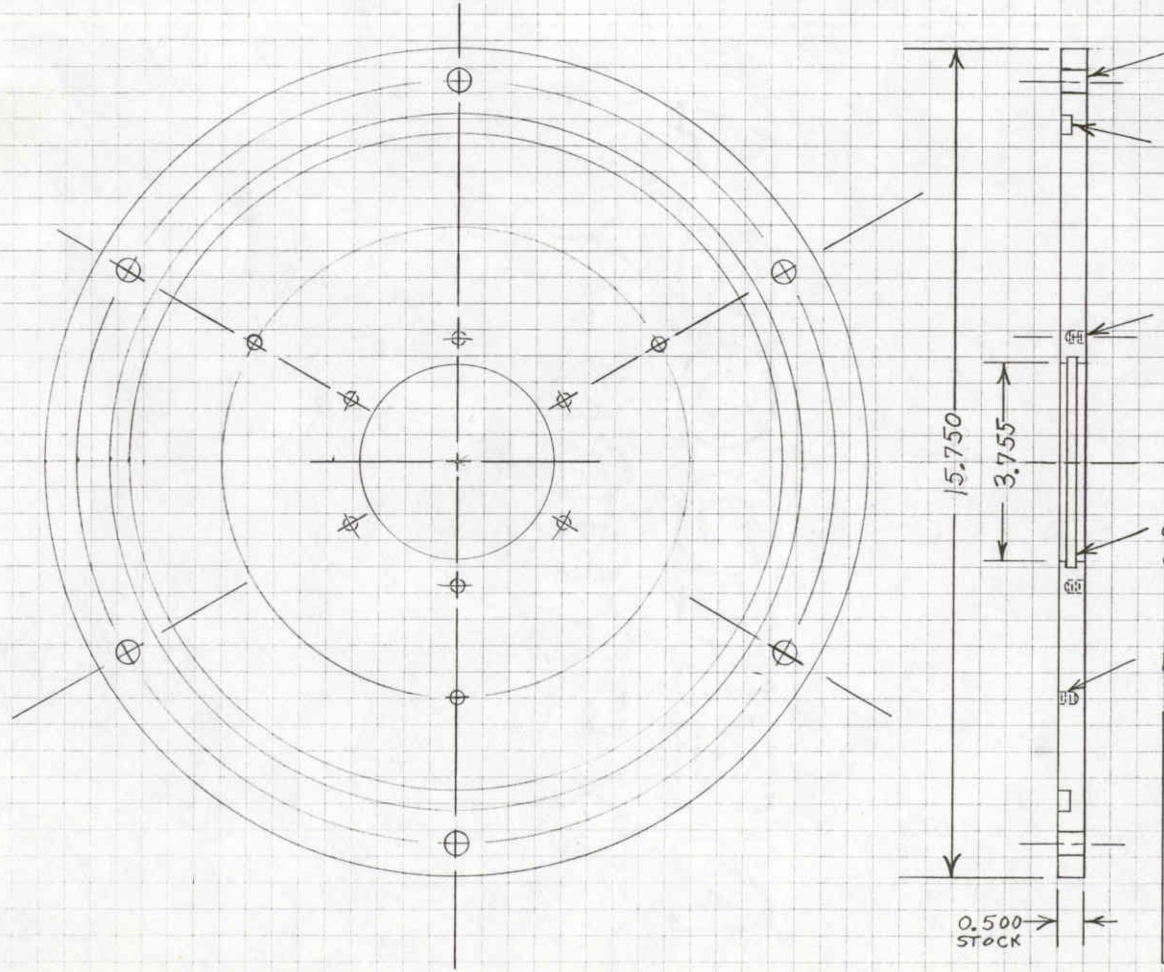


SOS CHERENKOV DETECTOR

PHOTOTUBE ASSEMBLY

FEB. 2, 1994 W.R. SMYTHE

1 OF 6



25/64 DRILL THROUGH, 6 PLACES EQUALLY SPACED, 14.500 D B.C.

O-RING GROOVE 12.600 ID x 0.312 W x 0.220 DEEP

D&T 1/4-20, 0.375 DEEP, 6 PLACES, EQUALLY SPACED, 4.750 B.C.

O-RING GROOVE 3.975 OD x 0.205 W CENTERED IN PLATE

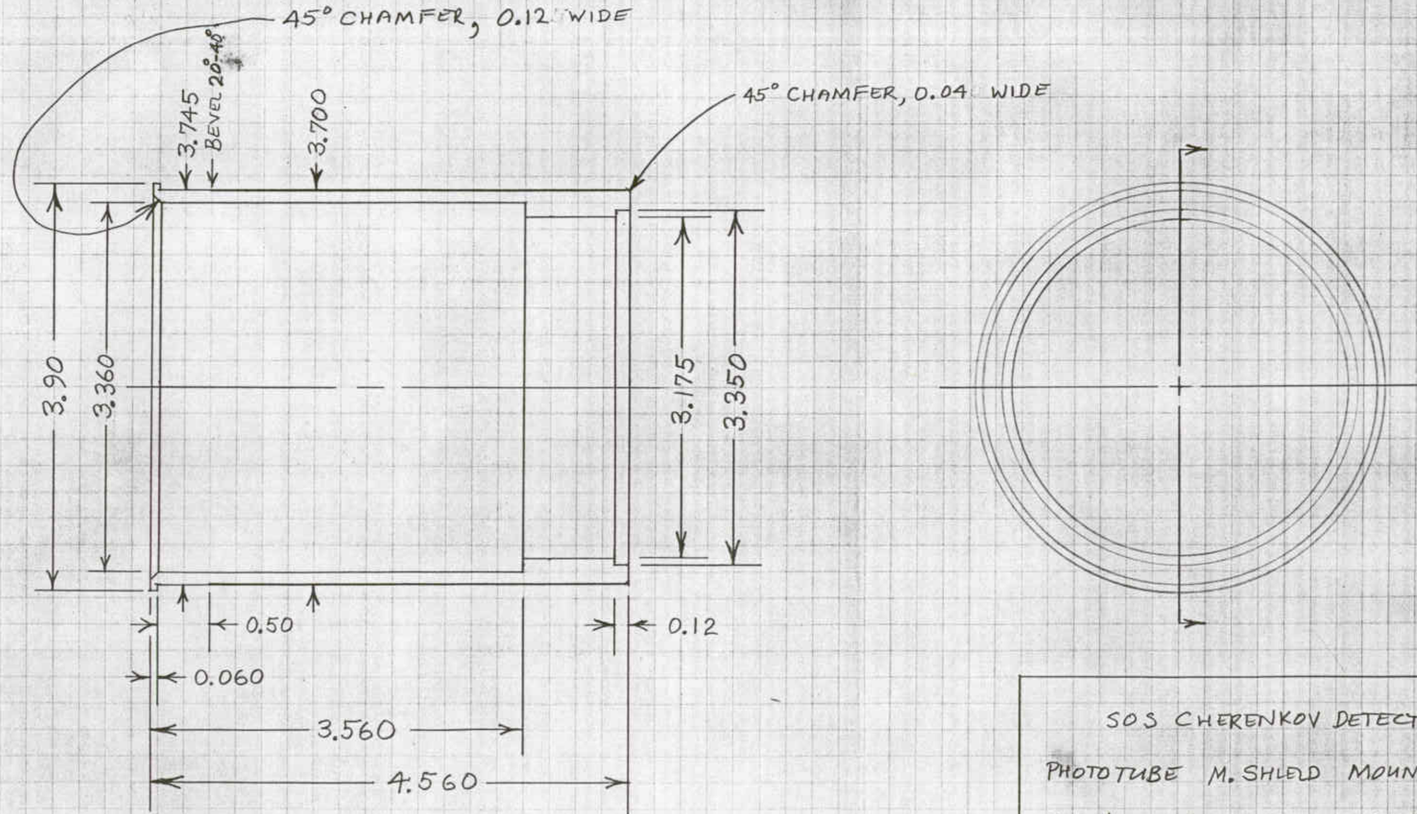
D&T 1/4-20, 0.375 DEEP, 3 PLACES, EQUALLY SPACED, 9.000 B.C.

SOS CERENKOV DETECTOR
PHOTO TUBE MOUNTING FLANGE

MATERIAL: ALUMINUM

4 REQ'D 2 OF 6

JAN 28, 1994 W. R. SMYTHE



SOS CHERENKOV DETECTOR

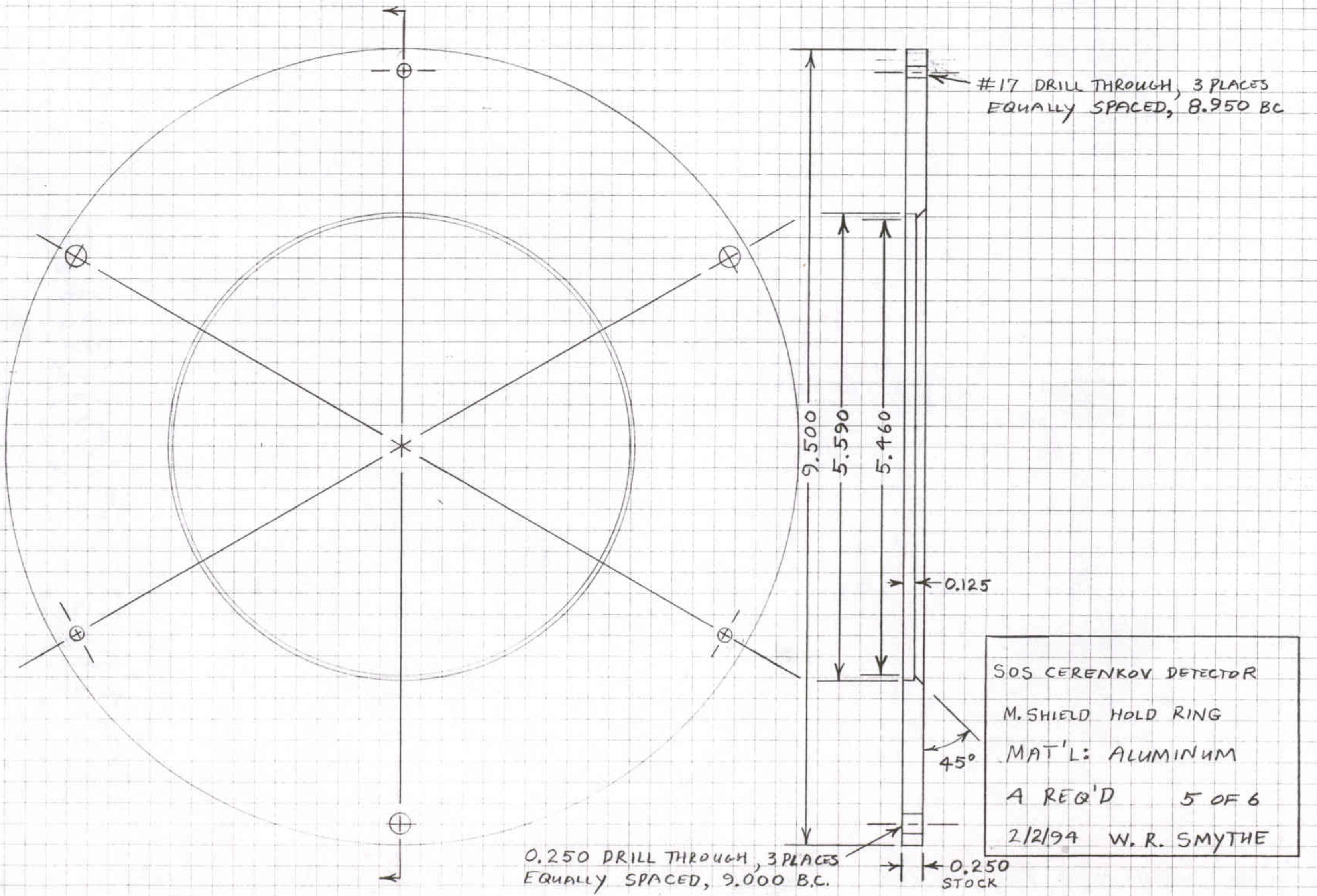
PHOTOTUBE M. SHIELD MOUNT, VER. 2

MAT'L. 6061 ALUMINUM

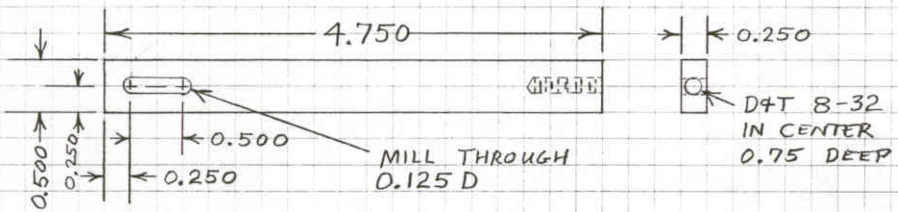
4 REQ'D W.R. SMYTHE

AUG 8, 1994 303-492-7772

(REPLACES DRAWINGS 3&4)

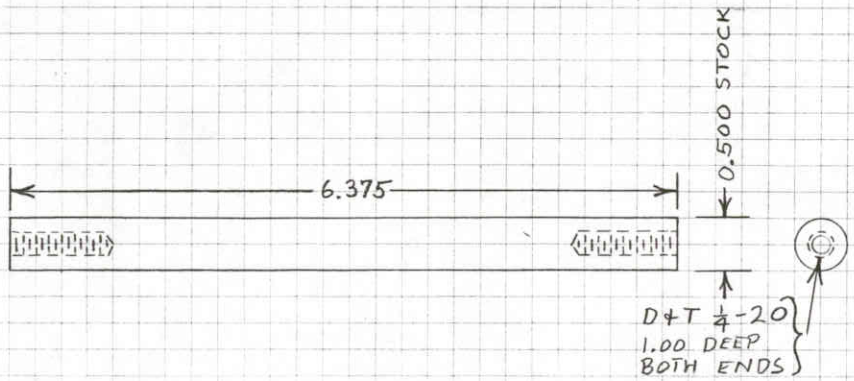


#17 DRILL THROUGH, 3 PLACES
EQUALLY SPACED, 8.950 BC
9.500
5.590
5.460
0.125
45°
0.250 DRILL THROUGH, 3 PLACES
EQUALLY SPACED, 9.000 B.C.
0.250
STOCK
SOS CERENKOV DETECTOR
M. SHIELD HOLD RING
MAT'L: ALUMINUM
4 REQ'D 5 OF 6
2/2/94 W. R. SMYTHE



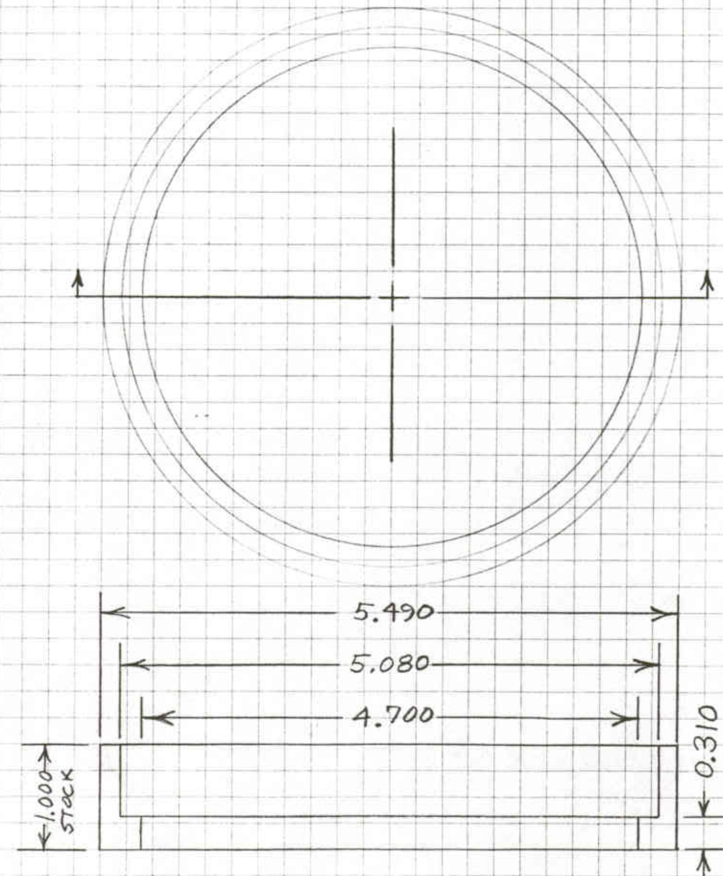
WINSTON CONE SUPPORT

MAT'L: ALUMINUM 12 REQ'D.



HOLD RING SUPPORT

MAT'L: ALUMINUM 12 REQ'D.



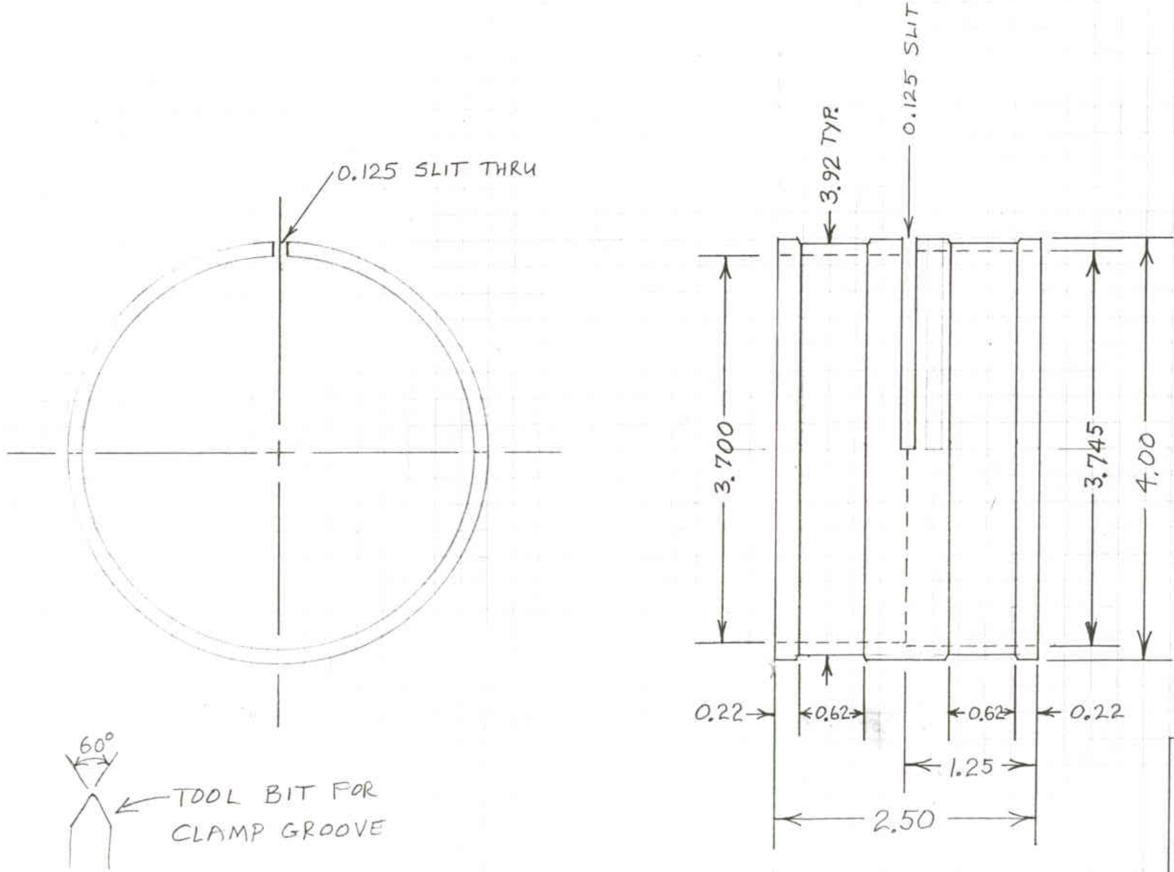
PHOTOTUBE SPACER RING

MAT'L: H.D. POLYETHYLENE 4 REQ'D.

SOS CHERENKOV DETECTOR

FEB. 2, 1994 W.R. SMYTHE

6 OF 6



PM TUBE BASE CLAMP

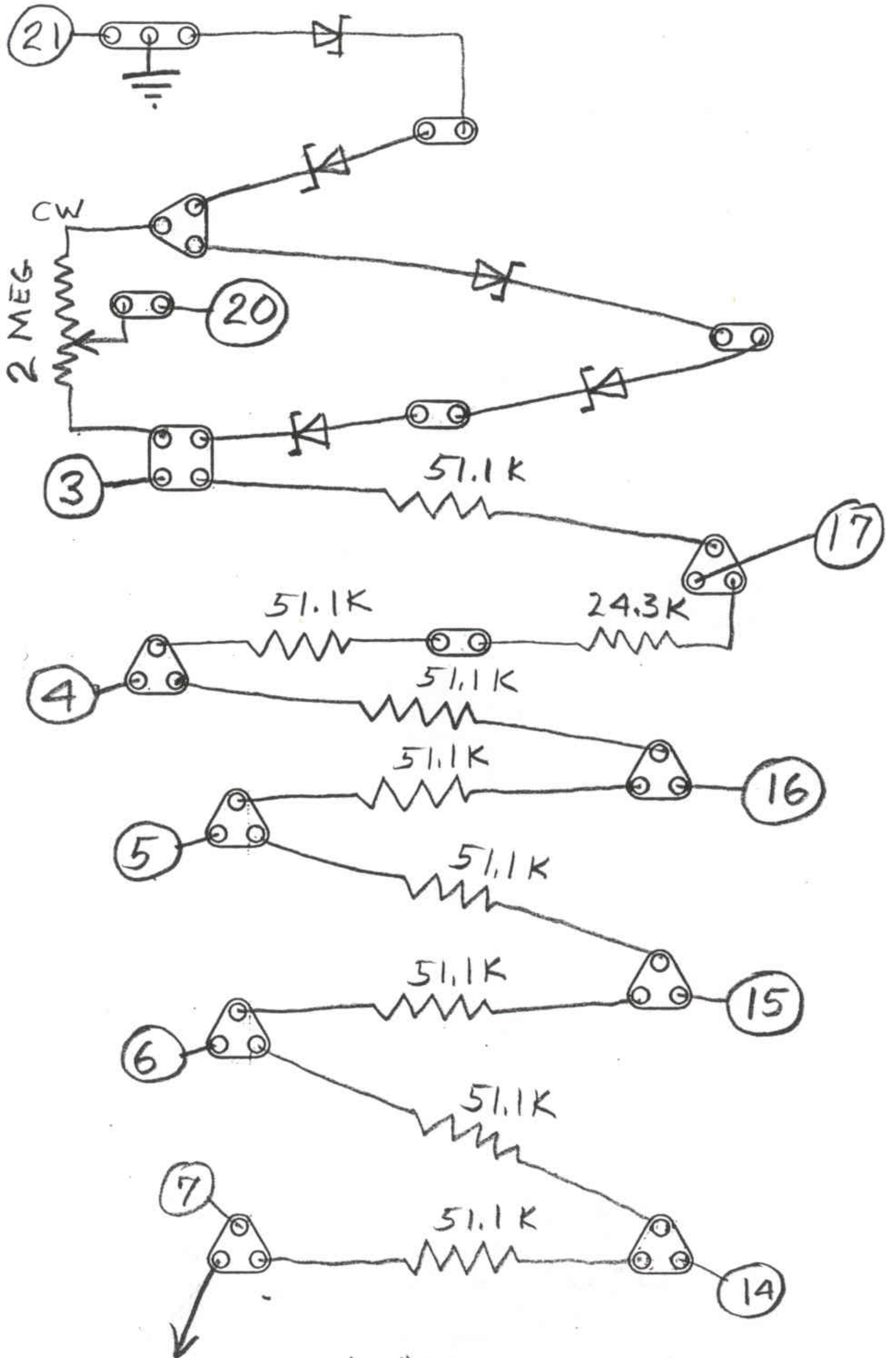
4 REQ'D ALUMINUM

W.R. SMYTHE AUG 8, 1994

8854 PHOTOTUBE BASE PC BOARD #2

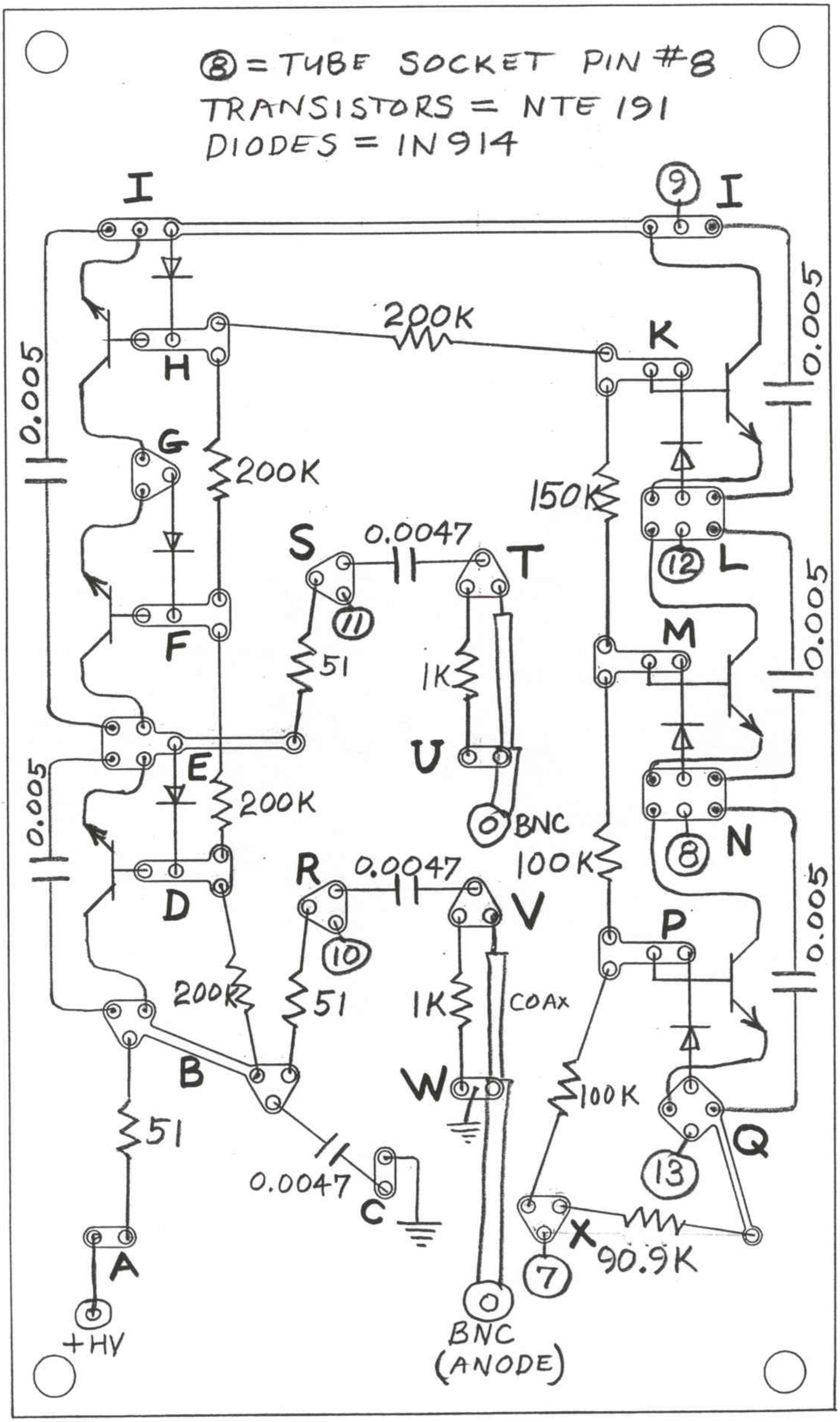
(15) = TUBE SOCKET PIN #15

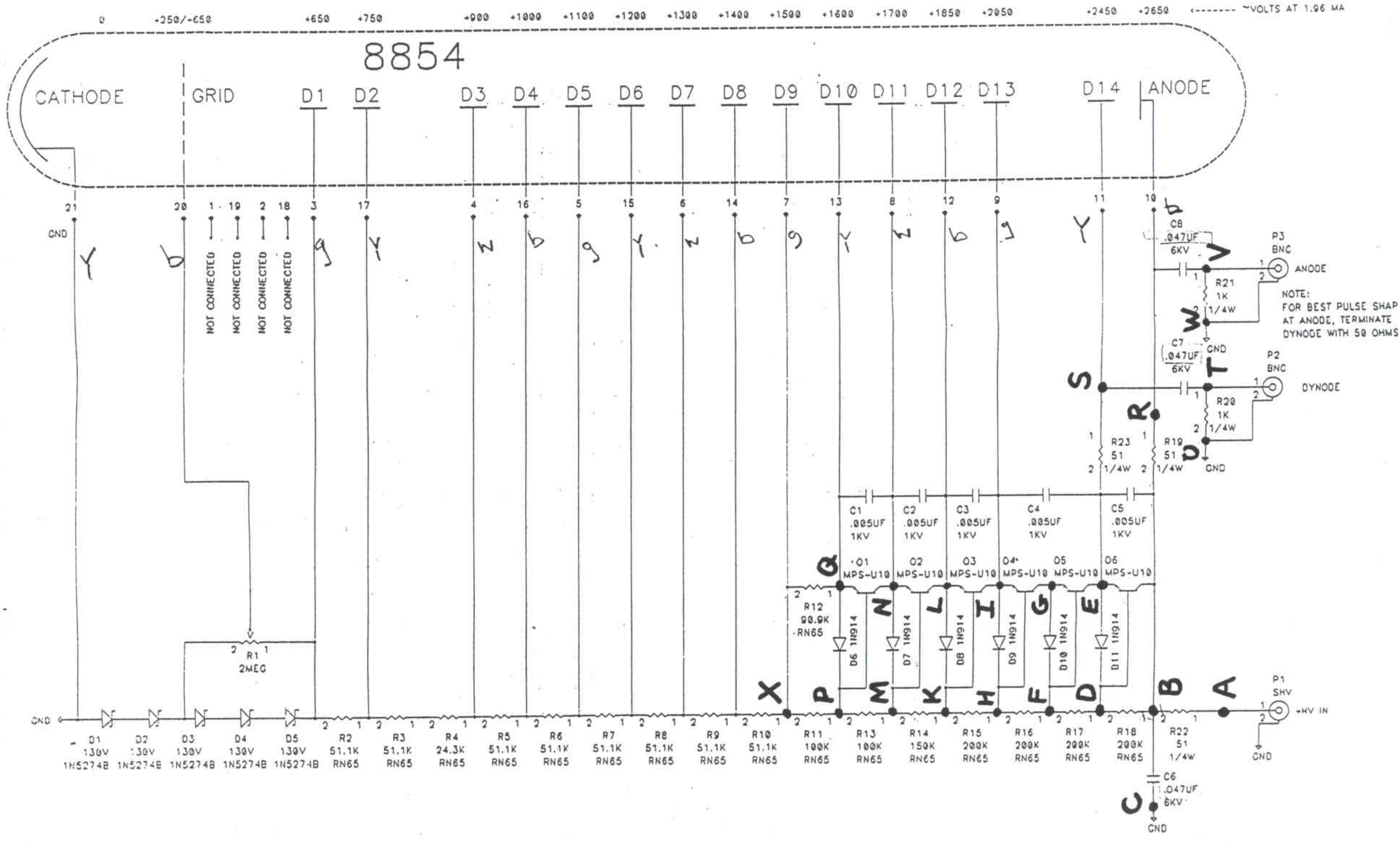
ZENER DIODES = 130 V, 1N5274B



TO POINT "X" ON OTHER PC BOARD

8854 PHOTOTUBE BASE PC BOARD #1





TAPER: /1/1.5/1/1/1/1/1/1/1/1/1.5/2/4/2/

...H ENERGY ...SICS GROUP HEPG UNIVERSITY OF ILLINOIS URBANA - CHAMPAIGN	DESIGNED BY: V.J.SIMAITIS	DATE DESIGNED: NOV 10 '76	USED ON: 8854....	TITLE: 8854.E1 8854 PMX BASE WITH EMITTER FOLLOWER - TYPE 1 BUILT ON XE14-B37,-B28,-B29,-B30	FILE: XEC	DRAWING NO.: XE14_C27	REV.:	DATE REVISED: SEP 4 '9...

IEEE Transactions on Nuclear Science, Vol.NS-24, No.1, February 1977

A HIGH-RATE PHOTOTUBE BASE

C. R. Kerns

Fermi National Accelerator Laboratory
Batavia, Illinois

Abstract

A photomultiplier tube base designed to minimize voltage changes at the phototube's dynodes under high-rate conditions is described. Over 200 of these phototube bases are presently used on lead glass and other calorimeter phototubes in high energy physics experiments. Stiff voltage sources for dynodes are provided by making use of emitter follower characteristics of high beta, high voltage, video transistors.

Introduction

Phototube bases designed for high-rate applications have historically made use of voltage regulator tubes, large capacitor banks[1] and divider string currents > 10^3 times larger than the time-averaged dynode current.[2] Other techniques include the use of cathode followers,[3] zener diodes,[4] miniature on-board Cockcroft-Walton power sources,[5] and the so-called afterburner technique[6] where additional power supplies are needed to supply stiff voltage to the last few dynodes of a phototube. All of these techniques may find use where they nicely solve a problem; in this paper a new type of high-rate base will be discussed which doesn't have a high-current string and therefore works effectively from the present high voltage zener divider distribution panels available at Fermilab.[7] This base is designed to minimize voltage changes in a phototube that would cause gain instability.

Circuit Design

Although high-rate bases have been produced for a variety of phototube types, i.e. 56 AVP, 6342A, 6655A, 8575, the concept is generally applicable to any photomultiplier. Figure 1 is the schematic of a phototube base designed for the 8575 and will serve well to demonstrate the design under discussion here. The concept will work for either high plus or high minus voltages; high minus is shown. Stiff voltage sources for dynodes are provided by making use of emitter follower characteristics of high beta, high voltage, video transistors. This is an "intelligent" power saving voltage divider: as the tube current increases, current is diverted from string to tube; instead of using a high string current, the transistor's beta provides an improvement factor as if the string current were more than 100 times greater than it is. For example, with the base illustrated in Figs. 1 and 2, with -2 kV H.V. and an 8575 phototube giving a gain of 2×10^7, it was measured that the required current from the -2 kV supply did not vary, and also the tube gain was held constant, for counting rates from zero to 10 MHz. As the count rate was increased, to light levels equivalent to 100 times the regulation limit, the average anode current at first rose to about twice the limit at counting rates of 10 MHz, and then fell (i. e. anode current overload protection was demonstrated).

Over a group of transistors purchased there will be a spread of betas. The high-beta transistors (e.g. $\beta = 150$) were put in the latter stages to get the best overall performance from the active voltage divider. The technique provides a lightweight, small size and simple base design not requiring voluminous energy-storage capacitors. The only capacitors needed are the usual ones for high-frequency bypassing.

The diodes placed at the base-emitter junction of the transistors are to prevent overvoltaging the transistor junction in the inverse direction, an effect that does not normally happen but could occur under fault conditions or during the transient turn-on or turn-off periods.

Various different tapers for the voltage division are possible at will; these are achieved by the proper choice of resistors at each stage in the resistor string shown in Fig. 1. If a particular interstage voltage is too high for one transistor, use two in

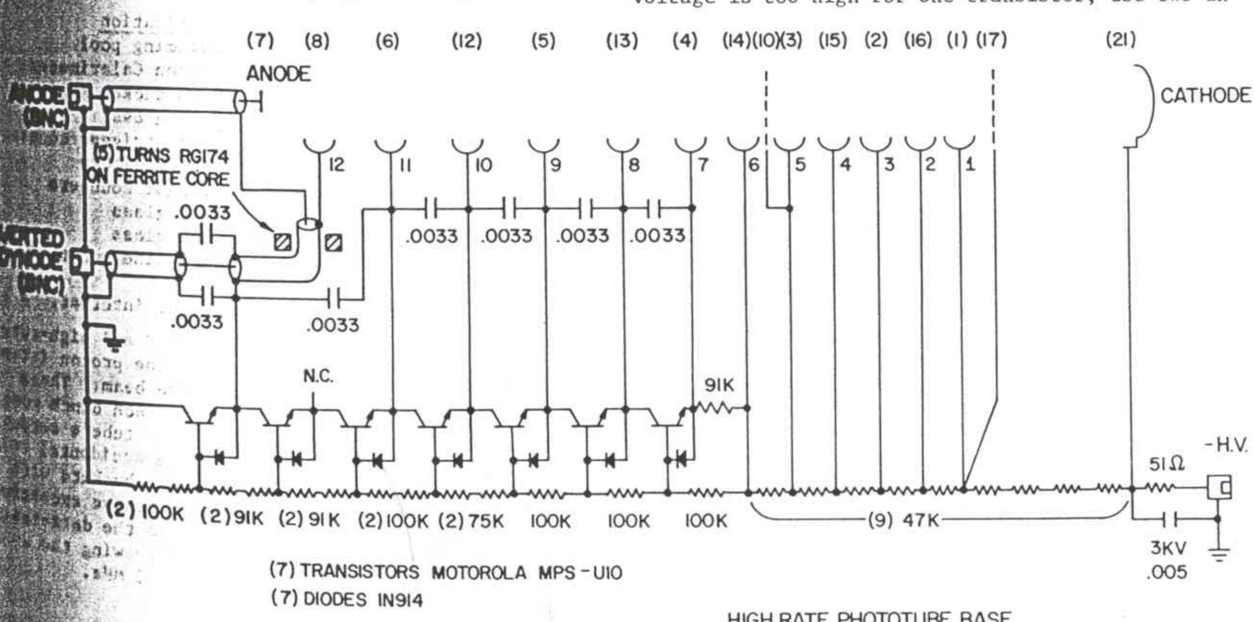


FIG. 1

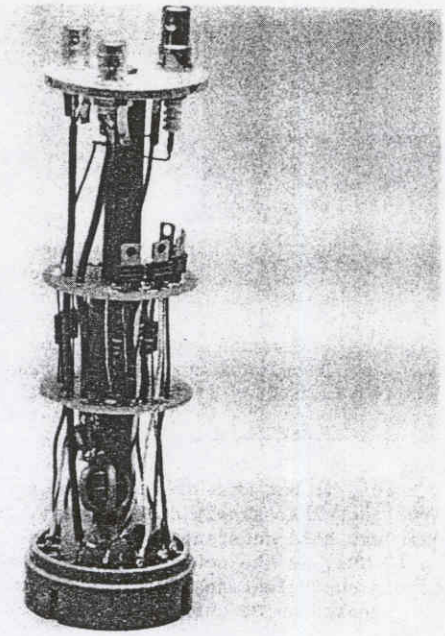


FIG. 2

series; Fig. 1 demonstrates (D_{11}-D_{12}) this principle, which can be extended at will to three, four, or --- transistors.

A feature of this base, not found in zener bases or after-burner systems, is worth mentioning. Suppose you wish to change the phototube voltage---the voltage division "tracks" over the whole voltage range with a single voltage adjustment, just like an ordinary simple resistive divider. With a zener base, of course, the voltage on some tube elements stays constant, while others vary in some fashion as the supply voltage is adjusted. With afterburners, one has at least two separate power supplies to adjust, plus extra cables and connectors to contend with. Another point is lower cost; even if 10 transistors were used in each base, the cost is less than just the extra connector used with the afterburner let alone the rest of the electronics used with such a design. (The transistors, MPS-U10, are less than a dollar each).

NPN vs. PNP Transistors

The negative high voltage base of Fig. 1 could be described as a solid-state, active voltage divider. The designer is faced with the choice of using either NPN or PNP transistors. One could make the base with either type, however, it appears that certain advantages favor the NPN. (When suitable F.E.T.'s appear on the market, they should be tried.)

1) The stiff voltage action of the NPN transistor only applies over a purposely limited current range. This helps prevent destruction of phototubes; a base capable of supplying unlimited current is a booby-trap because if a phototube is accidentally exposed to an excessive amount of light, it may be damaged by the resultant high current. This current-limiting action carries the terminology "fold-back current limiting", i.e. the voltage holds constant from zero current to some level; for greater current loading the voltage sags. This foldback protection is obtained "naturally" with the use of NPN's in this circuit, whereas PNP's turn "ON" harder with more load current, instead of turning "OFF".

2) One does not need a transistor for every dynode stage if NPN's are used, but one does need a transistor for every dynode if one uses PNP's. Typically, one saves 8 out of 14 transistors by going NPN with say a 56 AVP phototube.

Disadvantages

Solid-state devices are used in the phototube base, hence radiation damage eventually may occur. So far this has not been a problem. In the course of time, we will doubtless accumulate more experience on this. If it becomes a problem, the transistors can be replaced at less than one dollar each.

Bench Testing

Tests were made on a phototube and base assembly, making use of an enclosure (dark box) setup as indicated in Fig. 3. Both a fast pulsed light source and a DC light simultaneously illuminated the phototube to evaluate the adequacy of the base assembly to withstand high count rates. From the test setup diagram (Fig. 3) one sees that the phototube output is split into two components.

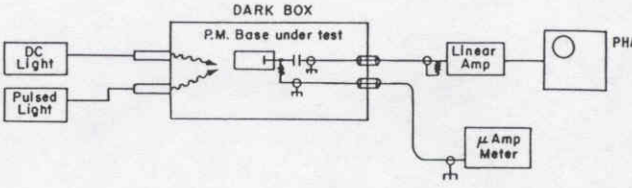


FIG. 3

The fast pulse component is capacitively coupled and terminated for monitoring pulse amplitude. The other component is directly coupled for monitoring the average anode current. Gain variation tests on various phototubes and base assemblies can be made with such a setup. Further details of this technique can be found in Ref. 8.

Experimental Applications

As indicated in the following table, a number of experiments here at Fermilab are presently using this high-rate phototube base.

Experiment	Tube Type	Application
E288/494	8575	Swimming pool Hadron Calorimeter
E288/494	56AVP	Beam Bucket Monitor
E456	8055	Lead glass
E456	6655A	Misc. trigger counters
E456	8575	Beam monitors
E456	56AVP	Trigger counters
E95	6342A	Lead glass
E290	8055	Lead glass
Meson Lab	56AVP	Beam line monitors

The E288/494 "bucket monitor" is of interest. A gas Čerenkov counter viewed with a 56AVP and high-rate base is used to give a measure of the proton intensity in each 1-2 ns wide RF bunch in the beam. These bunches are spaced by about 19 ns; each bunch contains from 1-1000 or so protons. The phototube's output enables the experimenters to reduce accidental coincidence rate problems by eliminating buckets with anomolously large numbers of protons; these excessively large bunches are digitized and veto the data-taking trigger. Figure 4 is a photograph showing the anode pulses from this tube operating at 53 MHz.

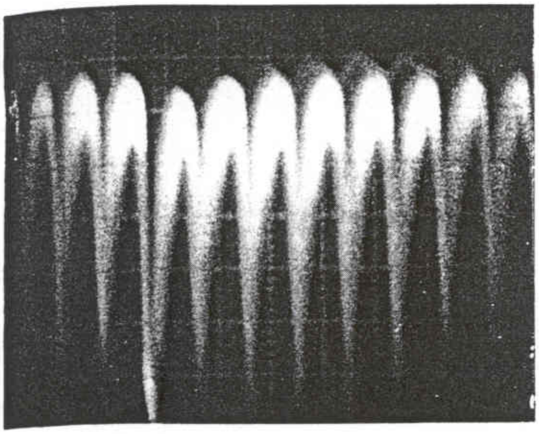


FIG. 4

A Parting Thought

This high rate base was designed to solve a particular problem given to me. While preparing references for this paper, I discovered a paper by H. Jung and M. Brullmann[9] with similar concepts. I suspect that there are still other independent discoverers and users of this idea; we have made sufficient use of it at Fermilab that I believed our experience will be useful to others.

References

[1] Gain Stability in High Current Photomultipliers at High Variable Counting Rates. A. K. Gupta and N. Nath, Nucl. Instrum. and Methods 53, 352 (1967).

[2] Die Zählratenabhängigkeit des Verstärkungsfaktors und des Auflösungsvermogens bei Photomultipliern Vom Typ RCA 6810A. W. Michaelis, H. Schmidt and C. Weitkamp, Nucl. Instrum. and Methods 21, 65 (1963).

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[4] Linearity and Fatigue in Photomultipliers. A. Fenster, J. C. LeBlanc, W. B. Taylor, H. E. Johns, Rev. Sci. Instrum. (USA) 44, No. 6, p. 689-94 (June 1973).

[5] Phototube High-Voltage Supply for Experiments with Balloons, Rockets and Satellites. G. Wibbereny, H. Kunow. Report BMWF-FBW-68-24, Kiel Univ. Inst. für Reive und Angervandte Kern-physik W. Germany (April 1968) 100 pp.

[6] High Dynamic Range and High Reliability Power Supply Networks for Photomultipliers. A. Looten, Nucl. Instrum. and Methods 71, 141 (1969).

[7] High-Voltage Power for Multiplier Phototubes. G. Constantion and K. Bregger. File No. CC10-10A LBL Counting Handbook UCRL-3307 (Revised).

[8] Gain Stability Measurement Techniques for Calorimeter Phototubes. C. R. Kerns. Proceedings of the Calorimeter Workshop, Fermilab, Batavia, Illinois, May 1975, p. 143.

[9] Ein niederohmiger Spannungsteiler für Photomultiplier H. Jung und M. Brüllmann, Nucl. Instrum. and Methods 65, 178 (1968).